



**B.E DEGREE EXAMINATIONS: JUNE 2017**

(Regulation 2015)

Second Semester

**ELECTRONICS AND COMMUNICATION ENGINEERING**

U15ECT202 : Electron Devices

**COURSE OUTCOMES**

- CO1:** Recognize the concepts of Electron Ballistics  
**CO2:** Understand the principles of Semiconductor Physics  
**CO3:** Illustrate the characteristics of diodes, BJT,FET,MOSFET and their applications  
**CO4:** Develop skills to implement simple projects using the basic devices.

**Time: Three Hours**

**Maximum Marks: 100**

**Answer all the Questions:-**

**PART A (10 x 1 = 10 Marks)**

1. Match list I with list II and select the correct answer using the codes given below the list CO1 [K<sub>2</sub>]

List I	List II
A. The bending of path due to interaction of electric and magnetic fields	(i) $1.602 \times 10^{-19}$
B. mass of the electron in Kg	(ii) negatively charged
C. charge of the electron in coulombs	(iii) $9.107 \times 10^{-31}$
D. electron s are	(iv) cycloid in nature

- |    | A  | B   | C   | D  |
|----|----|-----|-----|----|
| a) | i  | ii  | iii | iv |
| b) | ii | iv  | iii | i  |
| c) | iv | iii | i   | ii |
| d) | iv | iii | ii  | i  |

2. Force on each electron in a magnetic field is CO1 [K<sub>2</sub>]

- |           |           |
|-----------|-----------|
| a) $BNqv$ | b) $Bqv$  |
| c) $Bq$   | d) $BNqL$ |

3. Pn junction diode CO2 [K<sub>3</sub>]

- |                                 |                              |
|---------------------------------|------------------------------|
| a) Can be used a multi vibrator | b) Can be used as oscillator |
| c) Can be used as rectifier     | d) Can be used a regulator   |



**PART B (10 x 2 = 20 Marks)**

**(Answer not more than 40 words)**

- |   |                       |
|---|-----------------------|
| 11. Define electrostatic deflection sensitivity of a cathode ray tube   | CO1 [K <sub>2</sub> ] |
| 12. What is the speed of an electron after it has moved through a potential difference of 500 V?                          | CO1 [K <sub>2</sub> ] |
| 13. Write the expression for conductivity in an extrinsic semiconductor   | CO2 [K <sub>2</sub> ] |
| 14. Calculate the diode current for the forward biased voltage of 0.6 at 25°C, if the reverse saturation current is 10μA. | CO2 [K <sub>2</sub> ] |
| 15. Compare FET and MOSFET.   | CO3 [K <sub>2</sub> ] |
| 16. When a FET acts as a voltage variable resistor?   | CO3 [K <sub>2</sub> ] |
| 17. What is tunneling phenomenon  | CO4 [K <sub>2</sub> ] |
| 18. Name two applications of photoconductive cells?   | CO3 [K <sub>2</sub> ] |
| 19. Define SSI, LSI, MSI and VLSI circuits.   | CO3 [K <sub>2</sub> ] |
| 20. List the steps involved in the construction of a MOSFET as an integrated circuit.                                     | CO4 [K <sub>2</sub> ] |

**Answer any FIVE Questions:-**

**PART C (5 x 14 = 70 Marks)**

**(Answer not more than 300 words)**

**Q.No. 21 is Compulsory**

- |  |                       |
|--|-----------------------|
| 21. With the neat diagram, explain the input and output characteristics of a CB configuration of transistor. | CO3 [K <sub>2</sub> ] |
| 22. Draw the block diagram of a Cathode ray oscilloscope and explain its working                             | CO1 [K <sub>2</sub> ] |
| 23. Draw the graph of V I characteristics PN junction diode and explain its features                         | CO2 [K <sub>2</sub> ] |
| 24. With neat diagram explain the constructional details and working principles of SCR.                      | CO3 [K <sub>2</sub> ] |
| 25. With suitable diagrams explain how integrated resistors are fabricated using Monolithic technology.      | CO3 [K <sub>2</sub> ] |
| 26. With relevant sketches explain the construction working and characteristics of tunnel diode.             | CO3 [K <sub>2</sub> ] |
| 27. Explain the operation of N channel JFET. Sketch and explain the drain characteristics.                   | CO3 [K <sub>2</sub> ] |

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